U.H.F. LINEAR POWER TRANSISTOR

N-P-N multi-emitter silicon planar epitaxial transistor primarily for use in linear u.h.f. amplifiers for television transposers and transmitters.

Features:
- guaranteed low intermodulation figures;
- gold metallization ensures excellent reliability.

The transistor has a ¼" capstan envelope with a moulded cap. All leads are isolated from the stud.

QUICK REFERENCE DATA

R.F. performance in linear amplifier

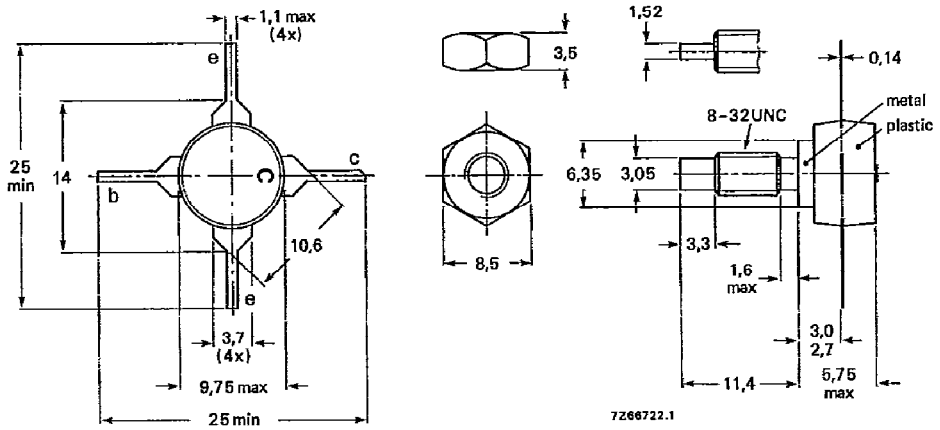
mode of operation	f_{vision} MHz	V_{CE} V	I_C mA	T_h °C	d_{im}* dB	$P_{o\ sync}$* W	G_p dB
class-A	860	25	250	25	−60	> 0,5	> 6
class-A	860	25	250	25	−60	typ. 0,6	typ. 7

* Three-tone test method (vision carrier −8 dB, sound carrier −7 dB, sideband signal −16 dB), zero dB corresponds to peak sync level.

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-48/3.



Torque on nut: min. 0,75 Nm (7,5 kg cm)
max. 0,85 Nm (8,5 kg cm)

Diameter of clearance hole in heatsink: max. 4,2 mm.
Mounting hole to have no burrs at either end.
De-burring must leave surface flat; do not chamfer or countersink either end of hole.

When locking is required an adhesive is preferred instead of a lock washer.

PRODUCT SAFETY This device incorporates beryllium oxide, the dust of which is toxic. The device is entirely safe provided that the BeO disc is not damaged.